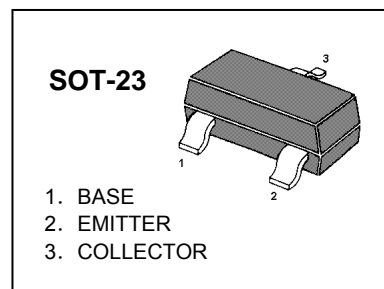


MMBTSC2412 TRANSISTOR (NPN)

FEATURES

- Low C_{ob} , $C_{ob} = 2.0$ pF (Typ).

MARKING : BR



MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current -Continuous	150	mA
P_C	Collector Power Dissipation	200	mW
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=50\mu\text{A}$, $I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}$, $I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=50\mu\text{A}$, $I_C=0$	7			V
Collector cut-off current	I_{CBO}	$V_{CB}=60\text{V}$, $I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=7\text{V}$, $I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=6\text{V}$, $I_C=1\text{mA}$	180		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50\text{mA}$, $I_B=5\text{mA}$			0.4	V
Transition frequency	f_T	$V_{CE}=12\text{V}$, $I_C=-2\text{mA}$, $f=100\text{MHz}$		160		MHz
Collector output capacitance	C_{ob}	$V_{CB}=12\text{V}$, $I_E=0$, $f=1\text{MHz}$		2.0	3.5	pF

Typical Characteristics

MMBTSC2412

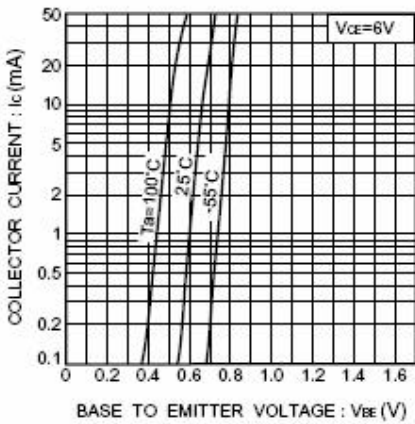


Fig.1 Grounded emitter propagation characteristics

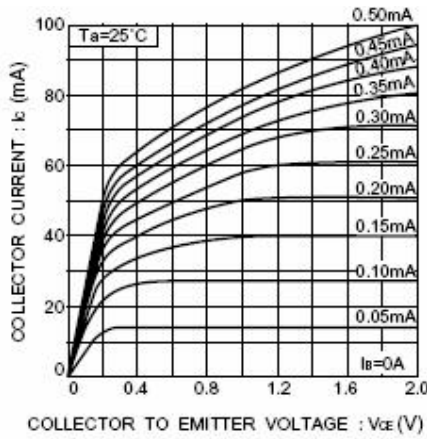


Fig.2 Grounded emitter output characteristics (I)

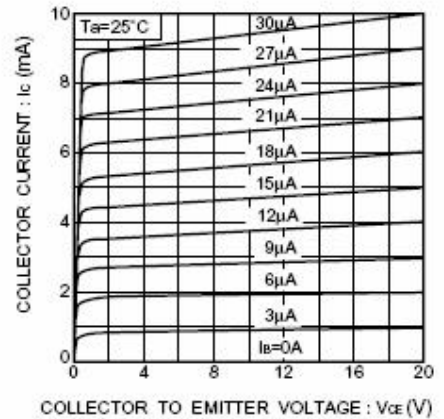


Fig.3 Grounded emitter output characteristics (II)

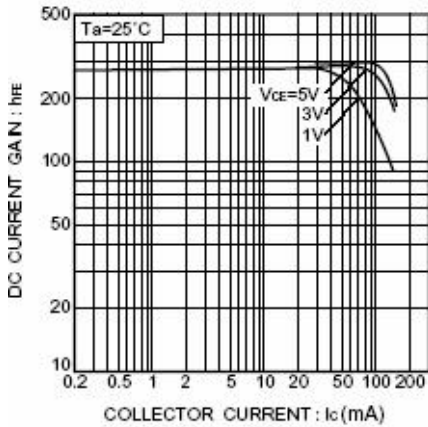


Fig.4 DC current gain vs. collector current (I)

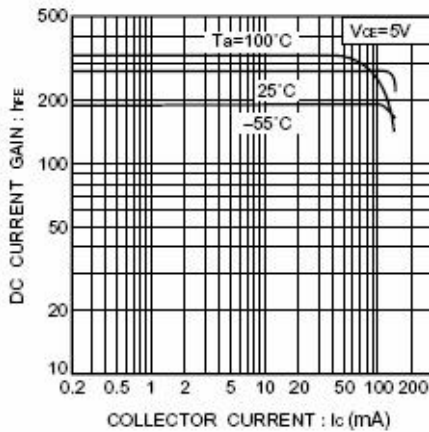


Fig.5 DC current gain vs. collector current (II)

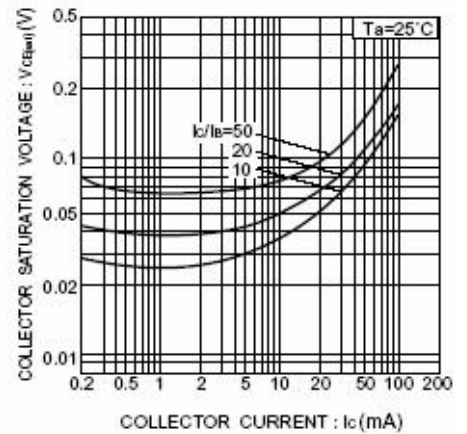


Fig.6 Collector-emitter saturation voltage vs. collector current

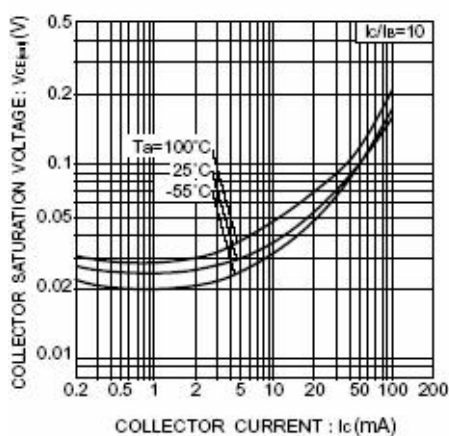


Fig.7 Collector-emitter saturation voltage vs. collector current (I)

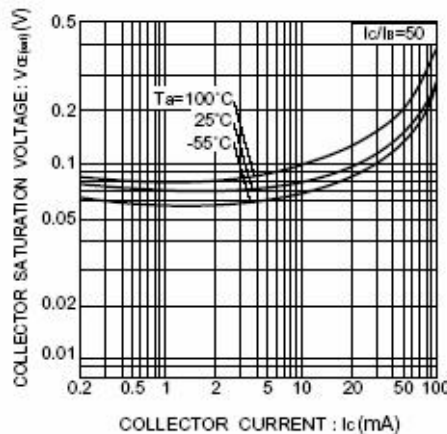


Fig.8 Collector-emitter saturation voltage vs. collector current (II)

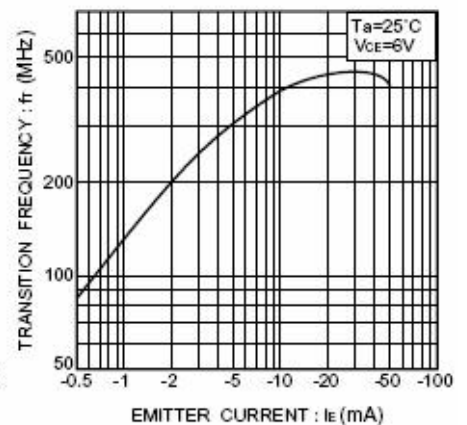


Fig.9 Gain bandwidth product vs. emitter current

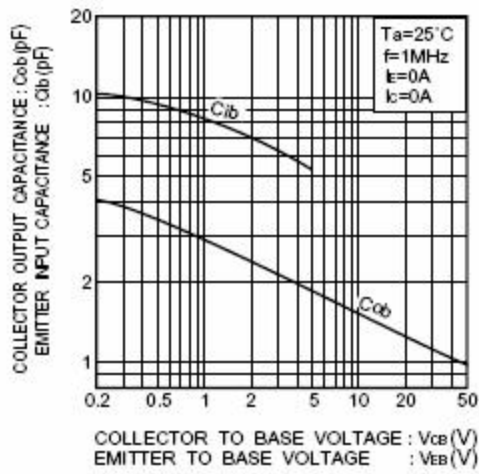


Fig.10 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

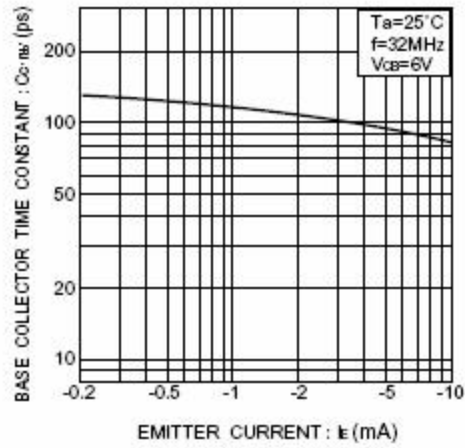


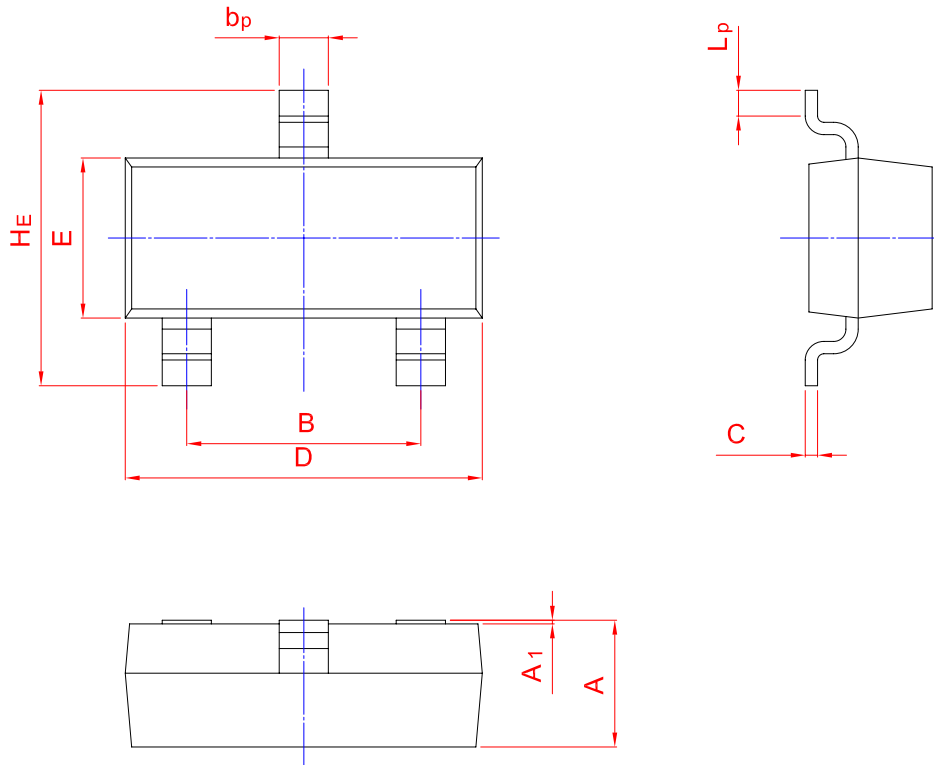
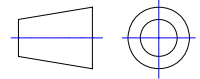
Fig.11 Base-collector time constant vs. emitter current



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b_p	C	D	E	$H\epsilon$	A_1	L_p
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20

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